

Wavelength range	Type	Technology	Electrodes
Infrared, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

<p style="text-align: center;">PD-02</p>	typ. dimensions (μm)	<b>Description</b> Infrared-selective photodiode with narrow response range (810 - 950 nm)
	typ. thickness 300 (±20) μm  <u>anode</u> gold alloy, 1.5 μm  <u>cathode</u> gold alloy, 0.5 μm	

## Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.17	mm <sup>2</sup>
Operating temperature range		$T_{amb}$	-40 to +125	°C
Storage temperature range		$T_{stg}$	-40 to +125	°C

## Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Dark current	$V_R = 1\text{ V}$	$I_D$		1.0	2.5	nA
Peak sensitivity	$V_R = 0\text{ V}$	$\lambda_P$		890		nm
Spectral range at 50 %	$V_R = 0\text{ V}$	$\lambda_{0.5}$	820		935	nm
Spectral bandwidth at 50%	$V_R = 0\text{ V}$	$\Delta\lambda_{0.5}$		115		nm
Responsivity at $\lambda_P^1$	$V_R = 0\text{ V}$	$S_\lambda$	0.15	0.25		A/W
Switching time	$V_R = 1\text{ V}$	$t_r, t_f$		15/30		ns

<sup>1</sup>Measured on bare chip on TO-18 header

## Labeling

Type	Typ. $I_D$ [pA]	Typ. $S_\lambda$ [A/W]	Lot N°	Quantity
EPC-880-0.5				

**Packing:** Chips on adhesive film with wire-bond side on top

\*Note: All measurements carried out with *EPIGAP* equipment

